



In re Application of:

H. WATANABE et al.

Serial No.: 09/320,271

Filed: May 27, 1999

For: SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF

RECEIVED
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

SEP -6 2001

TECHNOLOGY CENTER 2800

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Abal
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Group Art Unit: 2825

Examiner: C. Lee

AMENDMENT

Commission for Patents
Washington, D. C. 20231

September 4, 2001

Sir:

In response to the Office Action dated April 30, 2001, please amend the above- identified application as follows:

IN THE CLAIMS:

Please cancel non-elected claims 14-20 without prejudice or disclaimer.

Please amend claim 1 as follows:

1. (Twice Amended) A fabrication method of a semiconductor device comprising the steps of:
forming a first insulation layer over a substrate,
introducing impurities into said first insulation layer,
forming a trench in said first insulation layer, and
embedding and forming a first conductive layer in said trench.